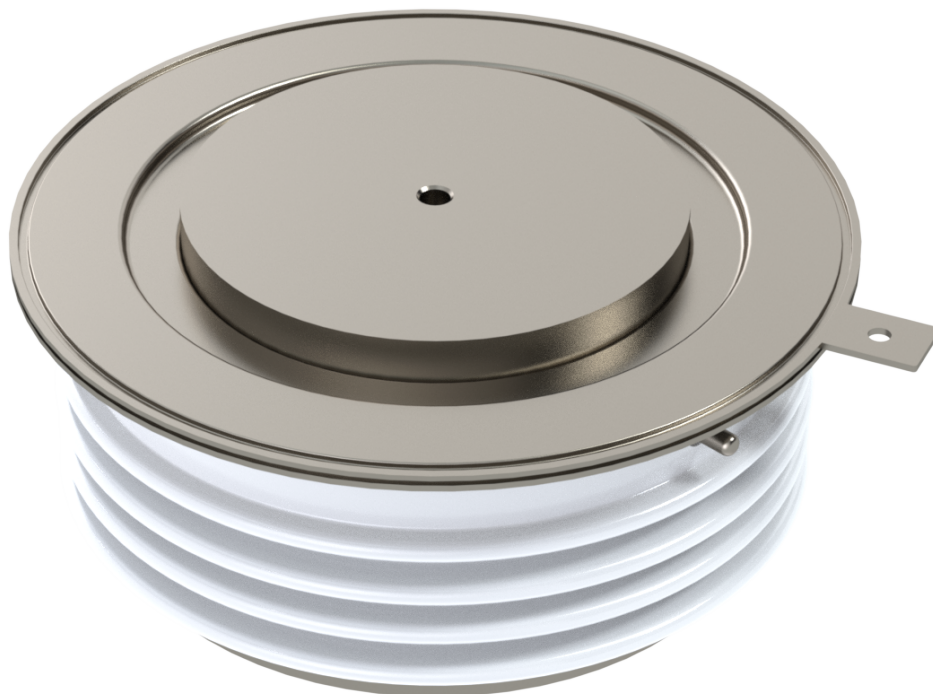


Distributed Gate Thyristor Type SA14YP0717EG

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Date: September, 2020
Data Sheet Issue: 1



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SA	14	YP	0717	E	G	
-	Voltage Code	Outline Code	Current code	Type code	t _q code	Optional code
t _q code: G = 35μs, H = 40μs						

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Absolute Maximum Ratings

VOLTAGE RATINGS		MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	1400	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	1400	V
V_{DDC}	Maximum DC of-state voltage, (note 1)	930	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	1400	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	1500	V
V_{RDC}	Maximum DC reverse voltage, (note 1)	930	V
note 1)	De-rating factor of 0.13%/°C is applicable for T_j below 25°C		

OTHER RATINGS		MAXIMUM LIMITS	UNITS
$I_{T(AV)M}$	Maximum average on-state current, $T_{sink} = 55^\circ\text{C}$, (note 1)	717	A
$I_{T(AV)M}$	Maximum average on-state current, $T_{sink} = 85^\circ\text{C}$, (note 1)	477	A
$I_{T(AV)M}$	Maximum average on-state current, $T_{sink} = 85^\circ\text{C}$, (note 2)	277	A
$I_{T(RMS)}$	Nominal RMS on-state current, $T_{sink} = 25^\circ\text{C}$ (note 1)	1439	A
$I_{T(d.c.)}$	D.C. on-state current, $T_{sink} = 25^\circ\text{C}$, (note 3)	1191	A
I_{TSM}	Peak non-repetitive surge current $t_p = 10\text{ms}$, $V_{RM} = 60\%V_{RRM}$, (note4)	7.05	kA
I_{TSM2}	Peak non-repetitive surge current $t_p = 10\text{ms}$, $V_{RM} \leq 10\text{V}$, (note 4)	7.80	kA
I^2t	I^2t capacity for fusing $t_p = 10\text{ms}$, $V_{RM} = 60\%V_{RRM}$, (note 4)	$248.5 \cdot 10^3$	A^2s
I^2t	I^2t capacity for fusing $t_p = 10\text{ms}$, $V_{RM} \leq 10\text{V}$, (note 4)	$304.2 \cdot 10^3$	A^2s
$(di/dt)_{cr}$	Critical rate of rise of on-state current (repetitive), (note 5)	1000	$\text{A}/\mu\text{s}$
	Critical rate of rise of on-state current (non repetitive), (note 5)	1500	$\text{A}/\mu\text{s}$
V_{RGM}	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	2	W
P_{GM}	Peak forward gate power	30	W
T_{jop}	Operating temperature range	-40 to +125	$^\circ\text{C}$
T_{stg}	Storage temperature range	-40 to +150	$^\circ\text{C}$
note 1)	Double-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 2)	Single-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 3)	Double-side cooled		
note 4)	Half-sinewave, 125°C T_j initial		
note 5)	$V_D = 67\%V_{DRM}$, $I_{FG} = 2\text{A}$, $t_R \leq 0.5\mu\text{s}$, $T_{case} = 125^\circ\text{C}$		

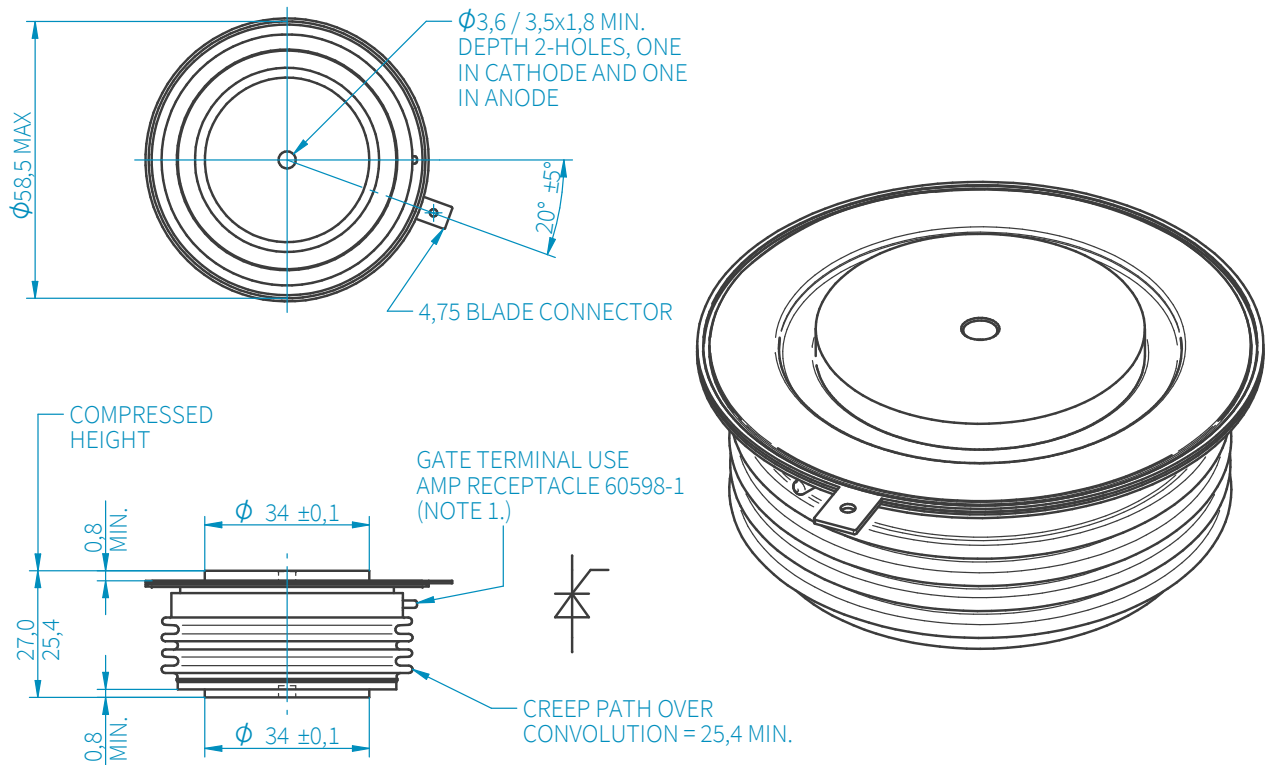
Characteristics

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
V_{TM}	Maximum peak on-state voltage	$I_{TM} = 1400A$	-	-	2.8	V
V_{T0}	Threshold voltage		-	-	1.752	V
r_T	Slope resistance		-	-	0.732	mΩ
$(dv/dt)_{CR}$	Critical rate of rise of off-state voltage	$V_D = 80\%V_{DRM}$, Linear ramp, Gate o/c	200	-	-	V/μs
I_{DRM}	Peak off-state current	Rated V_{DRM}	-	-	70	mA
I_{RRM}	Peak reverse current	Rated V_{RRM}	-	-	70	mA
V_{GT}	Gate trigger voltage	$T_j = 25^\circ C$, $V_D = 10V$, $I_T = 2A$	-	-	3.0	V
I_{GT}	Gate trigger current		-	-	300	mA
V_{GD}	Gate non-trigger voltage	Rated V_{DRM}	-	-	0.25	V
I_H	Holding current	$T_j = 25^\circ C$	-	-	1000	mA
t_{GD}	Gate controlled turn-on delay time	$V_D = 67\%V_{DRM}$, $I_{TM} = 1000A$, $di/dt = 60A/\mu s$,	-	-	-	μs
t_{GT}	Turn-on time	$I_{FG} = 2A$, $t_r = 0.5\mu s$, $T_j = 25^\circ C$	-	-	-	μs
Q_{RR}	Recovered charge		-	425	-	μC
Q_{RA}	Recovered charge, 50% Chord	$I_{TM} = 1000A$, $t_p = 1000\mu s$, $di/dt = 60A/\mu s$,	-	150	200	μC
I_{RM}	Reverse recovery current	$V_R = 50V$	-	100	-	A
t_{RR}	Reverse recovery time		-	3.0	-	μs
t_{GQ}	Turn-off time (note 2)	$I_{TM} = 1000A$, $t_p = 1000\mu s$, $di/dt = 60A/\mu s$,	-	-	40	μs
		$V_R = 50V$, $V_{DR} = 33\%V_{DRM}$, $dV_{DR}/dt = 20V/\mu s$				
R_{thJK}	Thermal resistance, junction to sink (note 3)	Double-side cooled	-	-	0.032	K/W
		Single-side cooled	-	-	0.034	K/W
F	Mounting force	(note 3)	10	-	20	kN
W_t	Weight		-	340	-	g
note 1)	Unless otherwise indicated $T_j = 125^\circ C$					
note 2)	The required t_Q (specified with $dV_{DR}/dt = 200V/\mu s$) is 35μs					
note 3)	For other clamp forces, please consult factory					

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